

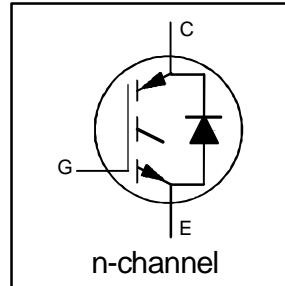
IRGP450UD2

INSULATED GATE BIPOLAR TRANSISTOR
WITH ULTRAFAST SOFT RECOVERY
DIODE

UltraFast CoPack IGBT

Features

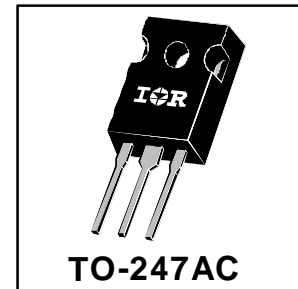
- Switching-loss rating includes all "tail" losses
- HEXFRED™ soft ultrafast diodes
- Optimized for high operating frequency (over 5kHz)



$V_{CES} = 500V$
$V_{CE(sat)} \leq 3.2V$
@ $V_{GE} = 15V, I_C = 33A$

Description

Co-packaged IGBTs are a natural extension of International Rectifier's well known IGBT line. They provide the convenience of an IGBT and an ultrafast recovery diode in one package, resulting in substantial benefits to a host of high-voltage, high-current, motor control, UPS and power supply applications.



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	500	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	59	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	33	
I_{CM}	Pulsed Collector Current ①	120	
I_{LM}	Clamped Inductive Load Current ②	120	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	29	
I_{FM}	Diode Maximum Forward Current	120	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	200	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	78	
T_J	Operating Junction and	-55 to +150	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	—	—	0.64	°C/W
$R_{\theta JC}$	Junction-to-Case - Diode	—	—	0.83	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	—	40	
Wt	Weight	—	6 (0.21)	—	g (oz)

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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage ③	500	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.41	—	V/°C	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	2.1	3.2	V	$I_C = 33A, V_{GE} = 15V$ $I_C = 59A$ $I_C = 33A, T_J = 150^\circ\text{C}$
		—	2.6	—		
		—	2.1	—		
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	5.5		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-10	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu A$
g_{fe}	Forward Transconductance ④	7.0	22	—	S	$V_{CE} = 100V, I_C = 33A$
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 500V$
		—	—	6500		$V_{GE} = 0V, V_{CE} = 500V, T_J = 150^\circ\text{C}$
V_{FM}	Diode Forward Voltage Drop	—	1.3	1.7	V	$I_C = 25A$
		—	1.2	1.5		$I_C = 25A, T_J = 150^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	
Q_g	Total Gate Charge (turn-on)	—	120	180	nC	$I_C = 33A$ $V_{CC} = 400V$	
Q_{ge}	Gate - Emitter Charge (turn-on)	—	22	33			
Q_{gc}	Gate - Collector Charge (turn-on)	—	41	62			
$t_{d(on)}$	Turn-On Delay Time	—	33	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 33A, V_{CC} = 400V$ $V_{GE} = 15V, R_G = 5.0\Omega$ Energy losses include "tail" and diode reverse recovery.	
t_r	Rise Time	—	26	—			
$t_{d(off)}$	Turn-Off Delay Time	—	110	170			
t_f	Fall Time	—	91	140			
E_{on}	Turn-On Switching Loss	—	0.91	—			
E_{off}	Turn-Off Switching Loss	—	0.25	—	mJ		
E_{ts}	Total Switching Loss	—	1.2	1.7			
$t_{d(on)}$	Turn-On Delay Time	—	37	—	ns	$T_J = 150^\circ\text{C}$, $I_C = 33A, V_{CC} = 400V$ $V_{GE} = 15V, R_G = 5.0\Omega$ Energy losses include "tail" and diode reverse recovery.	
t_r	Rise Time	—	29	—			
$t_{d(off)}$	Turn-Off Delay Time	—	160	—			
t_f	Fall Time	—	110	—			
E_{ts}	Total Switching Loss	—	1.8	—			
L_E	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package	
C_{ies}	Input Capacitance	—	2700	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ $f = 1.0MHz$	
C_{oes}	Output Capacitance	—	280	—			
C_{res}	Reverse Transfer Capacitance	—	34	—			
t_{rr}	Diode Reverse Recovery Time	—	50	75	ns	$T_J = 25^\circ\text{C}$	$I_F = 25A$ $V_R = 200V$ $di/dt = 200A/\mu s$
		—	105	160		$T_J = 125^\circ\text{C}$	
I_{rr}	Diode Peak Reverse Recovery Current	—	4.5	10	A	$T_J = 25^\circ\text{C}$	
		—	8.0	15		$T_J = 125^\circ\text{C}$	
Q_{rr}	Diode Reverse Recovery Charge	—	112	375	nC	$T_J = 25^\circ\text{C}$	
		—	420	1200		$T_J = 125^\circ\text{C}$	
$di_{(rec)M}/dt$	Diode Peak Rate of Fall of Recovery During t_b	—	250	—	A/ μs	$T_J = 25^\circ\text{C}$	
		—	160	—		$T_J = 125^\circ\text{C}$	

Notes: ① Repetitive rating; $V_{GE}=20V$, pulse width limited by max. junction temperature. (See fig. 20)

② $V_{CC}=80\%(V_{CES})$, $V_{GE}=20V$, $L=10\mu H$, $R_G=5.0\Omega$, (See fig. 19)

④ Pulse width 5.0 μs , single shot.

③ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.

Refer to Section D - page D-13 for Package Outline 3 - JEDEC Outline TO-247AC

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>